NSN 5961-01-077-2825



Unitized Semiconductor Devices - Page 1 of 1	G	roup
View Online at https://aerobasegroup.com/nsn/5961-01-077-2825		
Inclosure Material:		
Metal		
Overall Length:		
Between 0.240 inches and 0.290 inches		
Overall Height:		
Between 0.030 inches and 0.070 inches		
Overall Width:		
Between 0.115 inches and 0.160 inches		
Component Name And Quantity:		
2 transistor		
Mounting Method:		
Press fit		
Features Provided:		
Burn in and hermetically sealed case		
Semiconductor Material:		
Silicon all transistor		
Voltage Rating In Volts Per Characteristic:		
50.0 collector to base voltage, dc all transistor and 30.0 collector to emitter voltage, dc all transistor and 5.0 emitter voltage, dc all transistor and 5.0	to base voltage	e, dc all
transistor		
Current Rating Per Characteristic:		
300.00 milliamperes source cutoff current all transistor		
Power Rating Per Characteristic:		
350.0 milliwatts small-signal input power, common-collector absolute all transistor		
Maximum Operating Tempurature Per Measurement Point:		
200.0 degrees celsius junction		
Terminal Type And Quantity:		
6 ribbon		
Shelf Life:		
N/a		
Unit Of Measure:		
Demilitarization:		
No		
Fiig:		
A110a0		